

Material Composition Declaration

Package Information

Package	Package Weight (mg)	Terminal Finish	MSL Rating
SOT-323	6	Matte Tin (Sn)	1

Product Group

Type No.	Description
MMBD352W	Diode Schottky 10mA 7V
RB706F-40, RB715F, RB717F	Diode Schottky 30mA 40V
BAS70W / AW / CW / SW	Diode Schottky 70mA 70V
1SS372	Diode Schottky 100mA 10V
MMBD717W / AW / CW / SW	Diode Schottky 200mA 20V
BAT54W / AW / CW / SW	Diode Schottky 200mA 30V
MMBD330	Diode Schottky 200mA 30V
BAS40W / AW / CW / SW	Diode Schottky 200mA 40V
MMBD770	Diode Schottky 200mA 70V
1SS401	Diode Schottky 300mA 20V
RB461F	Diode Schottky 700mA 20V
DA204U	Diode Switching 100mA 20V
M1MA141K, M1MA141WA, M1MA141WK	Diode Switching 100mA 40V
DAN202U, DAN217U, DAP202U	Diode Switching 100mA 80V
M1MA142K, M1MA142WA, M1MA142WK	Diode Switching 100mA 80V
BAL99W, BAV70W, BAW56W	Diode Switching 200mA 75V
BAS16W, MMBD4148W	Diode Switching 200mA 100V
BAS19W – BAS21W	Diode Switching 200mA 120V – 250V
BAV99W	Diode Switching 215mA 70V
MMBD4448W	Diode Switching 250mA 75V
BZX84C2V4W – BZX84VC51W	Diode Zener 200mW
MMBZ5221BW – MMB5262BW	Diode Zener 200mW

Component	Material	Substance	CAS No.	Material Mass (%)	Material Mass (mg)	Component Mass (%)	Component Mass (mg)	PPM
Die	Doped Silicon*	Si	7440-21-3	100.00	0.100	1.67	0.100	16667
Wire Bond	Gold	Au	7440-57-5	100.00	0.010	0.17	0.010	1667
Leadframe	Ferrous Alloy	Fe	7439-89-6	56.40	1.188	35.11	2.107	198058
		Ni	7440-02-0	42.00	0.885			147490
		Mn	7439-96-5	0.80	0.017			2809
		Co	7440-48-4	0.50	0.011			1756
		Si	7440-21-3	0.30	0.006			1054
Die Bond	Silver Silicone	Ag	7440-22-4	80.00	0.046	0.95	0.057	7600
		Bisphenol F	28064-14-4	15.00	0.009			1425
		Glycidyl neodeconate	26761-45-5	5.00	0.003			475
Plating	Matte Tin	Sn	7440-31-5	100.00	0.110	1.83	0.110	18333
Encapsulation	EMC	Silica	7631-86-9	79.00	2.857	60.27	3.616	476107
		Epoxy Resin	29690-82-2	20.00	0.723			120533
		Carbon Black	1333-86-4	1.00	0.036			6027

Tolerance ±10%

*Dopant and metallization of the silicon die are not reported in this statement where their concentration is less than the minimum reportable level per EIA JIG-101.

Data disclosed herewith is approximate and is based on information from suppliers surveys, Material Safety Datasheet, engineering calculations and measurements. Won-Top Electronics(WTE) has checked all information carefully and believes it to be correct and accurate. However, WTE cannot assume any responsibility for inaccuracies. WTE reserves the right to change any or all information herein without further notice.

RoHS Declaration

The European Parliament and of the Council on the Restriction of the use of Certain Hazardous Substances in Electrical and Electronics Equipment (RoHS) directive restricts the concentration of Lead (Pb), Mercury (Hg), Hexavalent Chromium (Cr6+), Polybrominated Biphenyls (PBB), Polybrominated Diphenyl Ethers (PBD) to 0.1%(1000 PPM) and restricts the concentration of Cadmium (Cd) to 0.01%(100 PPM) in homogeneous materials of electronics products.

The product group listed above and the homogenous materials are compliant with the Directive 2011/65/EU. WTE warrants that all its packing, components and/or products supplied to the Customer and/or its affiliated companies or designated contractors do not contain these hazardous substances in quantity levels higher than or equal to the thresholds to this directive.

Exemptions as declared for the directive are:

- 7(a) Lead in high melting temperature type solders (i.e. lead-based alloys containing 85% by weight or more lead).
- 7(c)-I Lead in glass (applicable for glass passivated silicon die).